IN THE SPECIFICATION:

Please substitute the following paragraph for the paragraph starting at page 4, line 6 and ending at line 24.

In particular, a-Si films have a disposition that, where any nuclei-forming matters such as dust in the order of micrometers have adhered to the support surface or deposited-film surface, the dust serves as nuclei during deposition to cause the growth of "protuberances". Fig. 2 is a diagrammatic sectional view showing an example of such protuberances of a conventional electrophotographic photosensitive member. The photosensitive member shown therein is constituted of a support 201 having a conductive surface, and a photoconductive layer 202 and a surface layer 203 superposingly formed thereon. Inclusion of dust 204 in the course of forming this photoconductive layer 202 causes abnormal growth on the dust that serves as nuclei during the deposition of a film. Such protuberances 205 have the shape of reversed cones whose vertexes start from the nuclei, and have a disposition that they have a lower ability to retain electric charges than the normal area.

Please substitute the following paragraph for the paragraph starting at page 34, line 6 and ending at line 11.

In the reactor 6110 in the deposition system 6100, cylindrical supports 6112, heaters 6113 (heater 5113 in Fig. 5) for heating the supports, and a source gas feed pipe 6114 (source gas feed pipe 5114 in Fig. 5) are provided. A high-frequency power source 6120 (high

frequency power source 5120 in Fig. 5) is connected to the reactor via a high-frequency matching box 6115.

Please substitute the following paragraph for the paragraph starting at page 34, line 20 and ending at line 22.

The cylindrical supports 6112 are set on conductive supporting stands 6123 (conductive supporting stand 5123 in Fig. 5) and are thereby connected to the ground.

Please substitute the following paragraph for the paragraph starting at page 34, line 26 and ending at page 35, line 16.

The cylindrical supports 6112 are set in the reactor 6110, and the inside of the reactor 6110 is evacuated by means of an exhaust device (e.g., a vacuum pump; not shown). Subsequently, the temperature of each cylindrical support 6112 is controlled at a desired temperature of from 200°C to 450°C, and preferably from 250°C to 350°C, by means of the heaters 6113 for heating the supports. Next, in order that source gases for forming the photosensitive members are flowed into the reactor 6110, gas cylinder valves 5231 to 5236 and a leak valve (not shown) of the reactor are checked to make sure that they are closed, and also flow-in valves 5241 to 5246, flow-out valves 5251 to 5256 and an auxiliary valve 5260 are checked to make sure that they are opened. Then, a main valve 6118 (main valve 5118 in Fig. 5) is opened to evacuate the insides of the reactor 6110 and gas feed pipe 6116 (gas feed pipe 5116 in Fig. 5).

Please substitute the following paragraph for the paragraph starting at page 35, line 17 and ending at line 27.

Thereafter, at the time a vacuum gauge 6119 (vacuum gauge 5119 in Fig. 5) has been read to indicate a pressure of 0.5 mPa, the auxiliary valve 5260 and the flow-out valves 5251 to 5256 are closed. Then, valves 5231 to 5236 are opened so that gases are respectively introduced from gas cylinders 5221 to 5226, and each gas is controlled to have a pressure of 0.2 MPa by operating pressure controllers 5261 to 5266. Next, the flow-in valves 5241 to 5246 are slowly opened so that gases are respectively introduced into mass flow controllers 5211 to 5216.

Please substitute the following paragraph for the paragraph starting at page 36, line 5 and ending at page 37, line 2.

That is, at the time the cylindrical supports 6112 has had the desired temperature, some necessary ones among the flow-out valves 5251 to 5256 and the auxiliary valve 5260 are slowly opened so that desired source gases are fed into the reactor 6110 from the gas cylinders 5221 to 5226 through a gas feed pipe 6114. Next, the mass flow controllers 5211 to 5216 are operated so that each source gas is so adjusted as to flow at a desired rate. In that course, the opening of the main valve 6118 is adjusted while watching the vacuum gauge 6119 so that the pressure inside the reactor 6110 comes to a desired pressure of from 13.3 mPa to 1,330 Pa. A leak valve 5117 is additionally provided as shown in Fig. 5. At the time the inner pressure has become stable, a high-frequency power source 6120 is set at a desired electric power and, using, e.g., a VHF power source with a frequency of from 50 MHz to 450 MHz, e.g., 105 MHz,

high-frequency power is supplied to a cathode electrode 6111 through the high-frequency matching box 6115 to cause high-frequency glow discharge to take place. The source gases fed into the reactor 6110 are decomposed by the discharge energy thus generated, so that the desired first layer composed chiefly of silicon atoms is formed on the cylindrical support 6112.